

IN THE CLAIMS:

Amend claims 5 and 6 to read:

5. (Amended) The row decoder according to Claim 3, wherein

in the erase mode, the select voltage is a positive voltage, while the non-select voltage is  
a negative voltage; and

an absolute value the select voltage is equal to an absolute value of the negative voltage )

applied to [the substrate or well) of the nonvolatile semiconductor storage device.

6. (Amended) The row decoder according to Claim 4, wherein

in the erase mode, the select voltage is a positive voltage, while the non-select voltage is

a negative voltage; and

an absolute value the select voltage is equal to an absolute value of the negative voltage )

applied to [the substrate or well) of the nonvolatile semiconductor storage device.